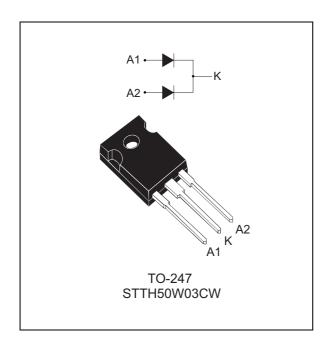
STTH50W03C



Turbo 2 ultrafast high voltage rectifier

Datasheet - production data



Description

The STTH50W03C uses ST Turbo 2 300 V technology. It is especially suited to be used for DC/DC and DC/AC converters in the secondary stage of MIG/MMA/TIG welding machines. Housed in ST's TO-247, this device offers high power integration for all welding machines and industrial applications.

Table 1. Device summary

Symbol	Value
I _{F(AV)}	2 x 25 A
V_{RRM}	300 V
t _{rr} (typ)	20 ns
T _j	175 °C
V _F (typ)	1 V

Features

- Ultrafast switching
- Low reverse recovery current
- · Low thermal resistance
- Reduces switching losses
- ECOPACK[®]2 compliant component

Characteristics STTH50W03C

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Table 2. Absolute ratings (limiting values per diode, at 25 °C, unless otherwise specified)

Symbol	Paramete	Value	Unit			
V_{RRM}	Repetitive peak reverse voltage	300	V			
I _{F(RMS)}	Forward rms current	40	Α			
	Average forward surrent S O E		Per diode	25	Α	
'F(AV)	$I_{F(AV)}$ Average forward current, $\delta = 0.5$	T _C = 100°C	Per device	50	A	
I _{FSM}	Surge non repetitive forward current	e non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			Α	
T _{stg}	Storage temperature range	-65 to + 175	° C			
T _j	Maximum operating junction tempera		+ 175	° C		

Table 3. Thermal resistance

Symbol	Parameter	Value	Unit	
P	Junction to case	Perdiode	1.8	
R _{th(j-c)} Junction to case	Junction to case	Total	1	°C / W
R _{th(c)}	Coupling		0.2	

When diodes 1 and 2 are used simultaneously:

 $Tj_{(diode\ 1)} = P_{(diode\ 1)} \times R_{th(j-c)}(Per\ diode) + P_{(diode\ 2)} \times R_{th(c)}$

Table 4. Static electrical characteristics per diode

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _R ⁽¹⁾	Reverse leakage	T _j = 25 °C	V –V			15	
'R	current	T _j = 125° C	$V_R = V_{RRM}$		15	150	μΑ
		$T_{j} = 25^{\circ} \text{ C}$ $T_{j} = 150 ^{\circ} \text{C}$ $T_{j} = 150 ^{\circ} \text{C}$			1.5		
V _F (2)	Forward voltage drop			1.0	1.2	V	
V _F V Forward voltage drop	T _j = 25° C	I 50 A			1.8	V	
		T _j = 150° C	I _F = 50 A		1.25	1.5	

^{1.} Pulse test: t_p = 5 ms, δ < 2%

To evaluate the conduction losses use the following equation:

$$P = 0.9 \text{ x I}_{F(AV)} + 0.012 \text{ I}_{F}^{2}_{(RMS)}$$

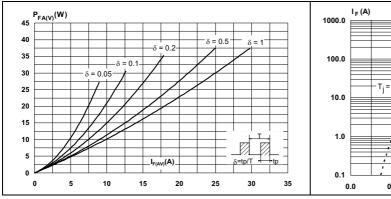
^{2.} Pulse test: t_p = 380 μ s, δ < 2%

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Symbol	Parameter	Test conditions			Тур	Max.	Unit
I _{RM}	Reverse recovery current		05 4 1/ 000 1/		7	9	Α
Q _{RR}	Reverse recovery charge	$T_j = 125 ^{\circ}\text{C}$ $I_F = 25 \text{A}, V_R = 200 \text{V}$ $I_F = 25 \text{A}, V_R = 200 \text{V}$ $I_F = 25 \text{A}, V_R = 200 \text{A}/\mu \text{S}$			170		nC
S _{factor}	Softness factor		αι _Γ /αι – -200 Α/μδ		0.3		
t _{rr}	Reverse recovery time	T _j = 25 °C	$I_F = 1 \text{ A}, V_R = 30 \text{ V}$ $dI_F/dt = -100 \text{ A/µs}$		20	27	ns
t _{fr}	Forward recovery time	T _i = 25 °C	I _F = 25 A, V _{FR} = 1.2 V			120	ns
V _{FP}	Forward recovery voltage	$dI_{F}/dt = 400 \text{ A/µs}$			2.5	3.6	V

Figure 1. Average forward power dissipation versus average forward current (per diode)

Figure 2. Forward voltage drop versus forward current (typical values, per diode)



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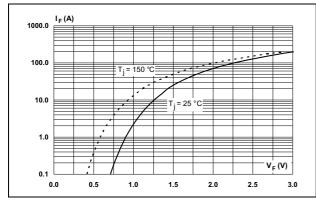
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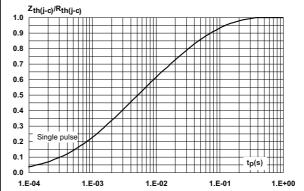
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Figure 3. Forward voltage drop versus forward current (maximum values, per diode)

Figure 4. Relative variation of thermal impedance junction to case versus pulse duration

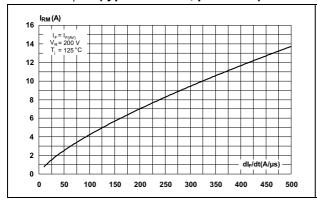




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Figure 5. Peak reverse recovery current versus dl_F/dt (typical values, per diode)

Figure 6. Reverse recovery time versus dl_F/dt (typical values, per diode)



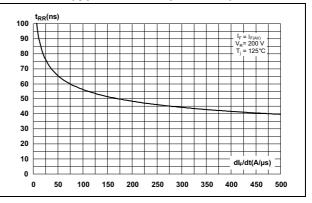
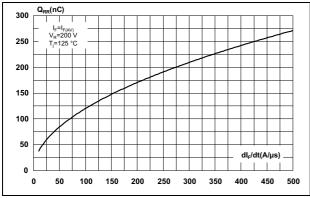


Figure 7. Reverse recovery charges versus dl_F/dt (typical values, per diode)

Figure 8. Reverse recovery softness factor versus dl_F/dt (typical values, per diode)



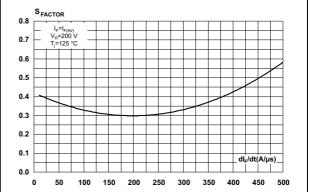
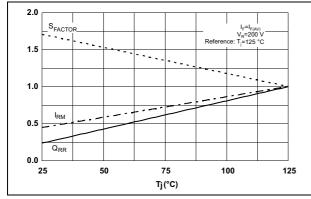
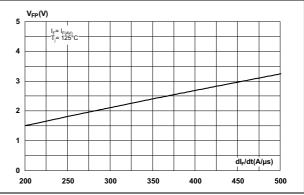


Figure 9. Relative variations of dynamic parameters versus junction temperature

Figure 10. Transient peak forward voltage versus dl_F/dt (typical values, per diode)

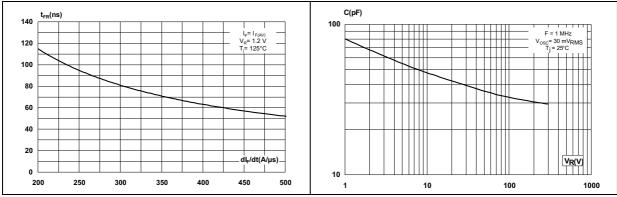




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STTH50W03C Characteristics

Figure 11. Forward recovery time versus dI_F/dt Figure 12. Junction capacitance versus reverse (typical values, per diode) voltage applied (typical values, per diode)





STTH50W03C **Package information**

Package information 2

Epoxy meets UL94, V0

Cooling method: by conduction (C)

Recommended torque value: 0.5 N·m

Maximum torque value: 1.0 N·m

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

L2 **1** L1 L3

Figure 13. TO-247 dimension definitions

Table 6. TO-247 dimension values

	Dimensions					
Ref.		Millimeters			Inches	
	Min.	Тур.	Max.	Min.	Тур	Max.
А	4.85		5.15	0.191		0.203
A1	2.20		2.60	0.086		0.102
b	1.00		1.40	0.039		0.055
b1	2.00		2.40	0.078		0.094
b2	3.00		3.40	0.118		0.133
С	0.40		0.80	0.015		0.031
D ⁽¹⁾	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
е	5.30	5.45	5.60	0.209	0.215	0.220
L	14.20		14.80	0.559		0.582
L1	3.70		4.30	0.145		0.169
L2		18.50 typ.			0.728 typ.	
ØP ⁽²⁾	3.55		3.65	0.139		0.143
ØR	4.50		5.50	0.177		0.217
S	5.30	5.50	5.70	0.209	0.216	0.224

^{1.} Dimension D plus gate protrusion does not exceed 20.5 mm.

^{2.} Resin thickness around the mounting hole is not less than 0.9 mm.

Ordering information STTH50W03C

3 Ordering information

Table 7. Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH50W03CW	STTH50W03CW	TO-247	4.46 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
09-Aug-2013	1	First issue.

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